



10.0mm (0.39") 7 Segment Display

- TOS-3191X Single Digit
- TOS-3192X Single Digit
- TOD-3291X Dual Digit
- TOD-3292X Dual Digit
- TOF-3491X Four Digit
- TOF-3492X Four Digit

Features

- * (0.39") 10.0mm DIGIT HEIGHT
- * CONTINUOUS UNIFORM SEGMENTS
- * LOW POWER REQUIREMENT
- * LOW CURRENT APPLICATION
- * EXCELLENT CHARACTER APPEARANCE
- * HIGH BRIGHTNESS & HIGH CONTRAST
- * WIDE VIEWING ANGLE
- * SOLID STATE RELIABILITY
- * RoHS COMPLIANT
- * Pb FREE
- * GRAY/BLACK FACE AVAILABLE



Absolute Maximum Rating

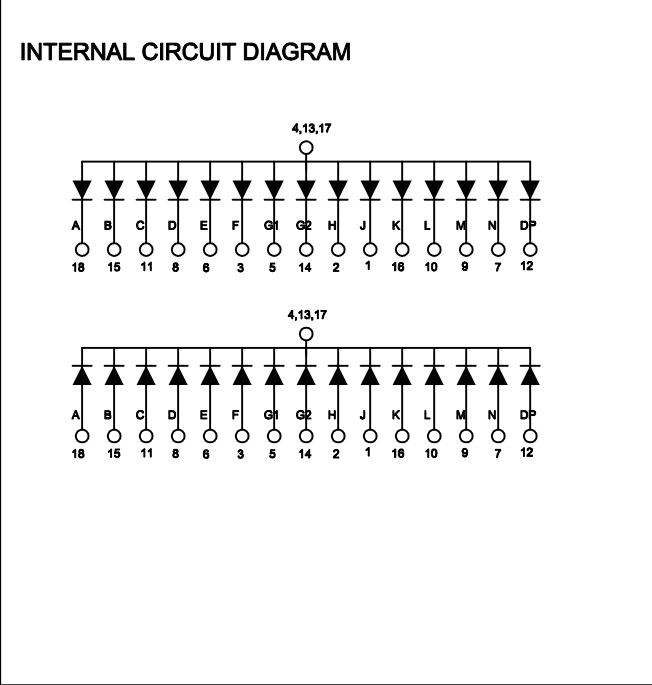
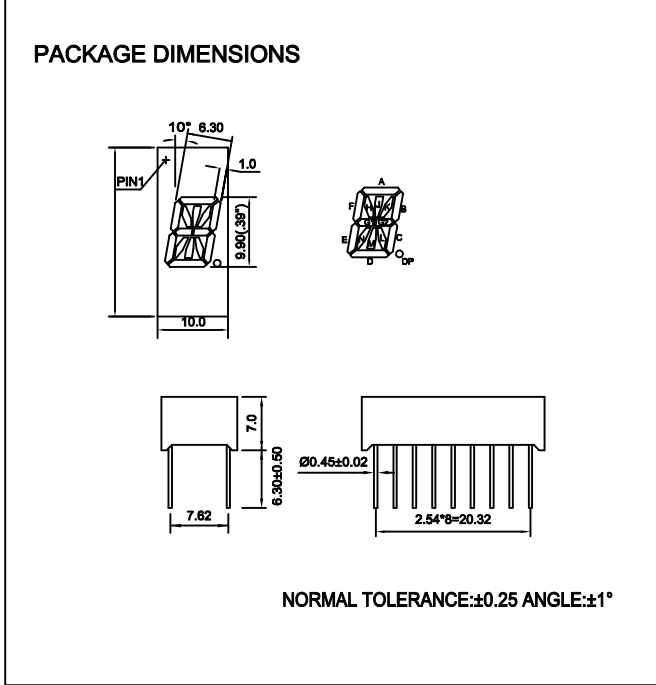
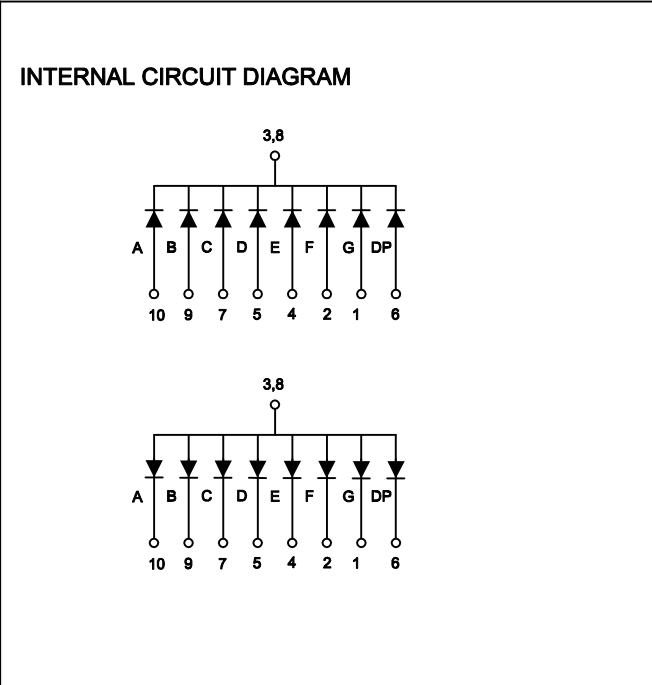
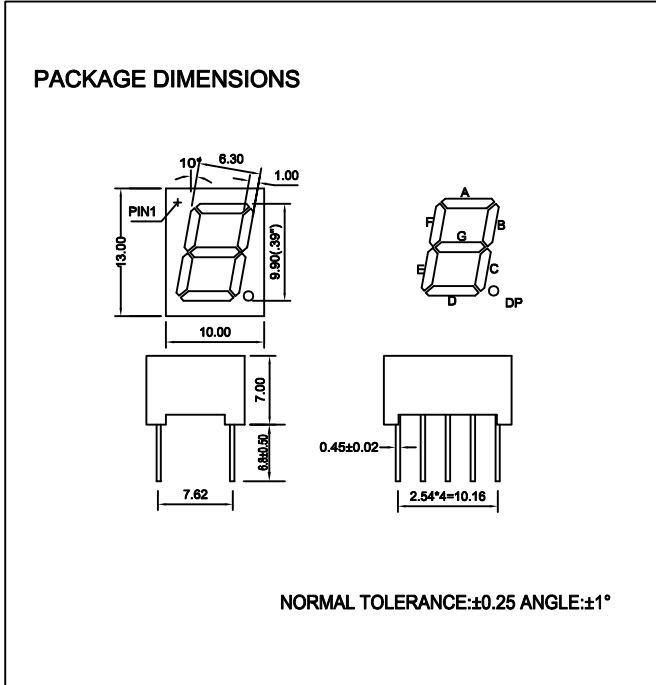
Series	Emitting color	Pd (mW)	If (mA)	IFP (mA)	VR (V)	Top (°C)	Tst (°C)	Tsol*2 (°C)	VF			λp	IV	
									IF (mA)	typ (V)	max (V)	typ (nm)	IF (mA)	typ (ucd)
0.39"	H	60	25	80	5	-25 ~ +85	-30 ~ +85	260/3Sec	20	1.8	2.0	660	10	1092
	S	60	25					260/3Sec	20	1.8	2.0	660	10	1530
	K	60	25					260/3Sec	20	1.8	2.0	648	10	1092

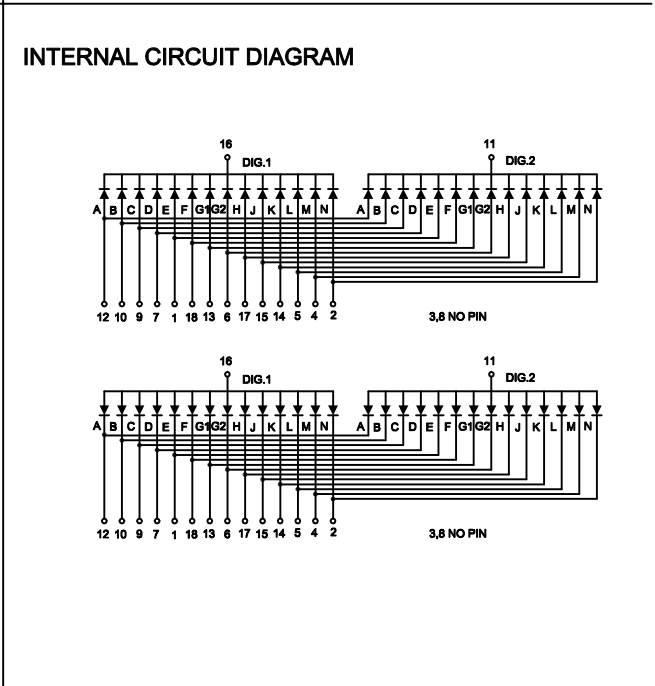
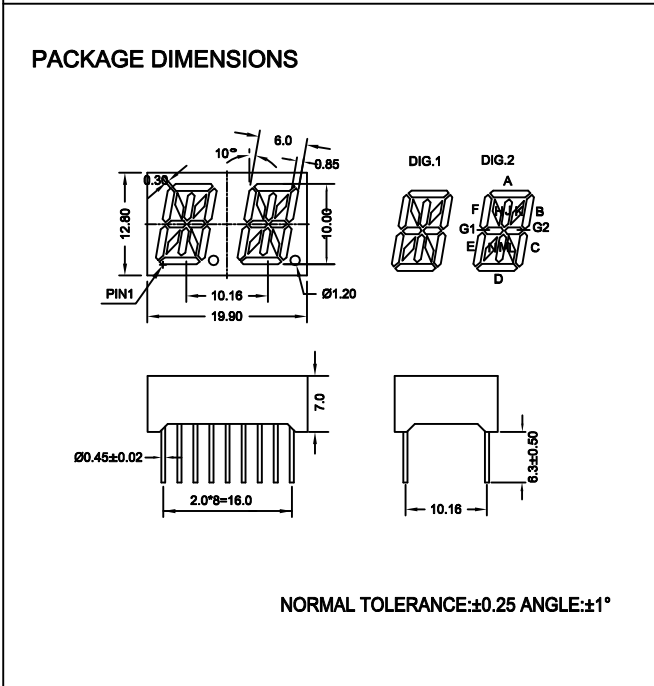
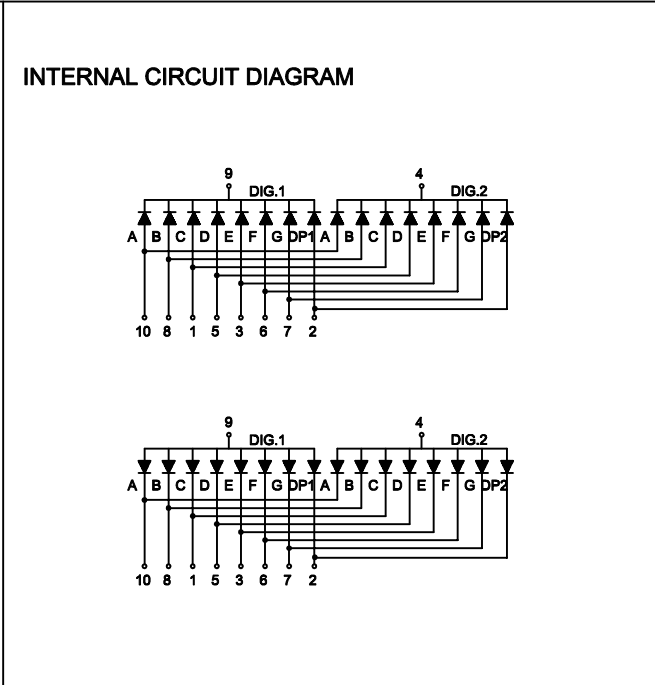
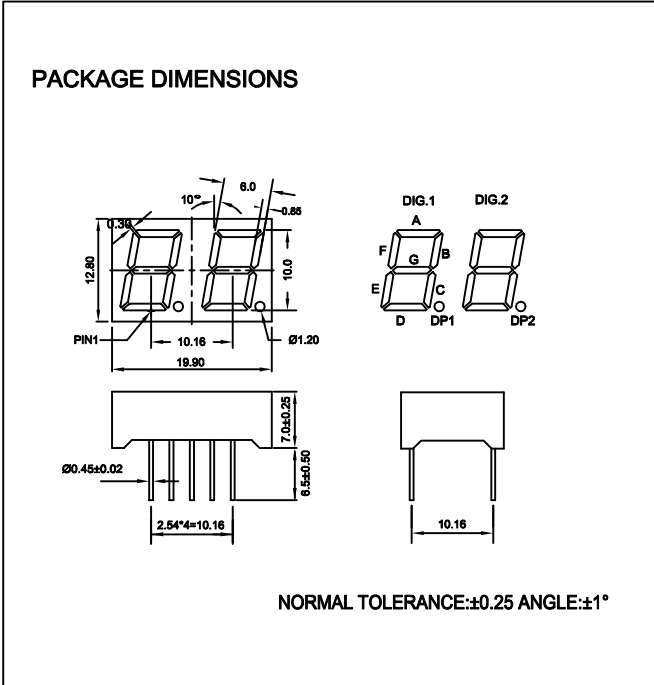
*1. Condition for IFP is pulse of 1 / 10 duty and 0.1 msec width.

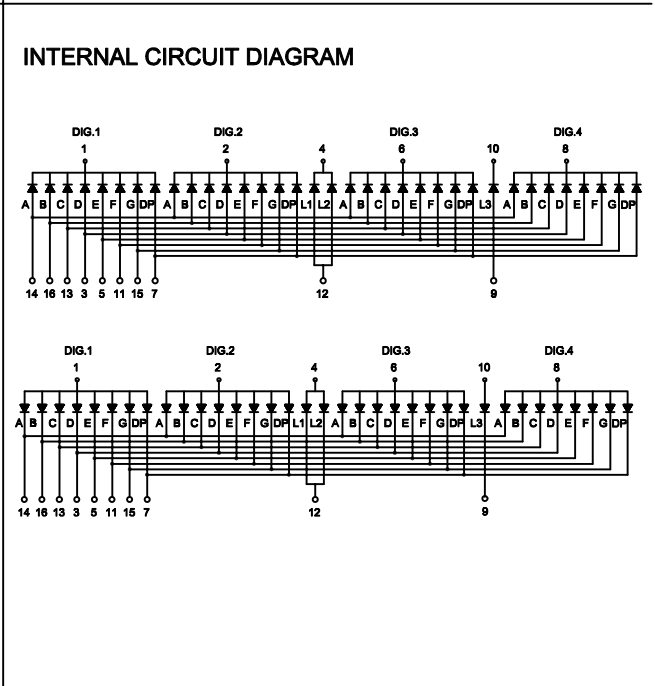
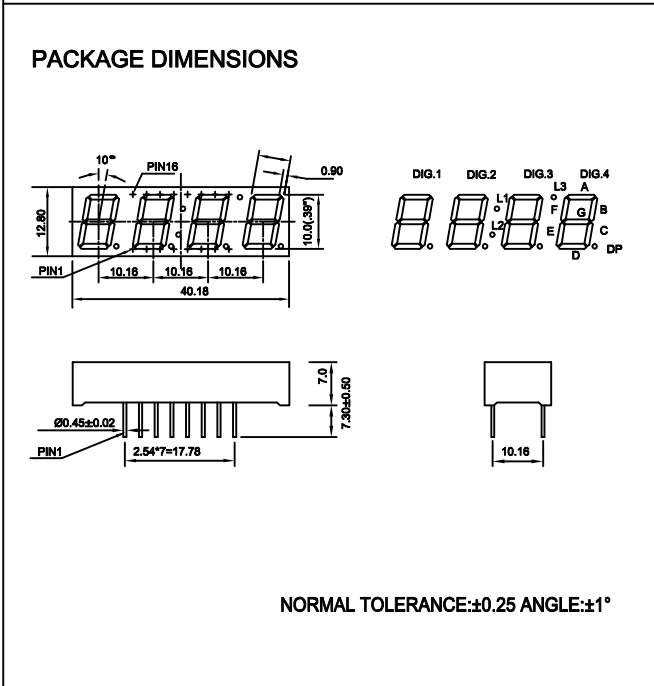
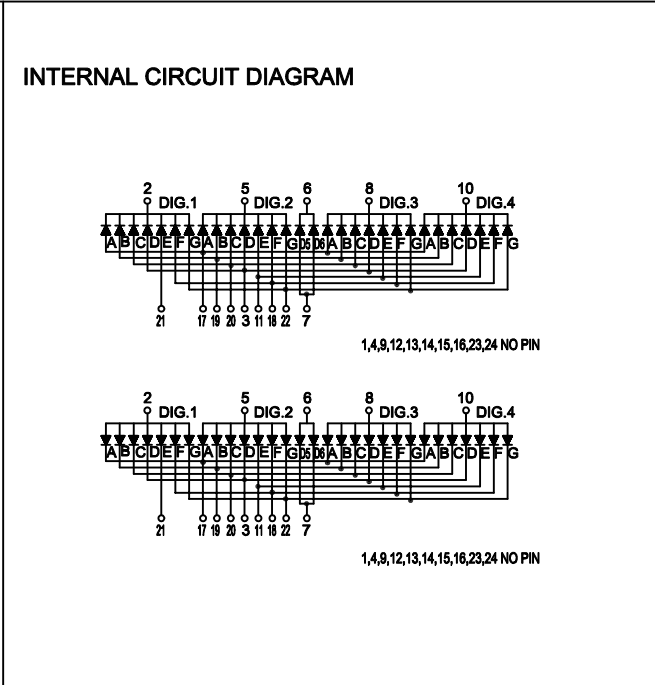
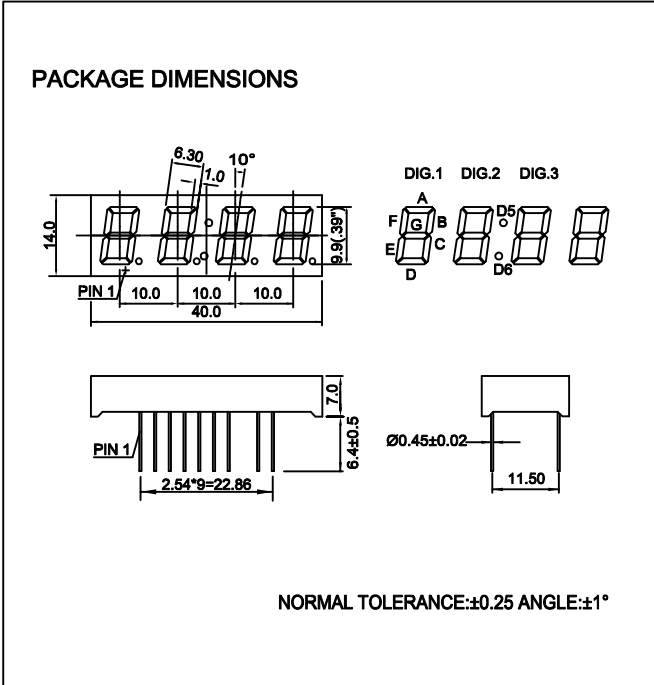
*2. Pb Free Process.

*3. In the absence of confirmation by device specification sheets, OASIS takes no responsibility for any defects that may occur in equipment using any OASIS devices shown in catalogs, data books, etc. Contact OASIS in order to obtain the latest device specification sheets before using any OASIS devices.

*4. Specifications are subject to change without notice for improvement.









Chip Material

H(Hi-red): GaAlAs/GaAs

S(Super-red): GaAlAs/GaAs

K(Hi-Orange): GaAlAs/GaAs

ABSOLUTE MAXIMUM RATING :(TA=25°C)

SYMBOL	PARAMETER	VALUE			UNITS
		H	S	K	
Pd	Power Dissipation Per Segment	60			mW
IFP	Peak Forward Current Per Segment (1/10 Duty Cycle, 0.1ms Pulse Width)	80			mA
IFM	Continuous Forward Current Per Segment	25			mA
TOP	Reverse Voltage Per Segment	5			V
TST	Operating Temperature Range	-25 to +85			°C
VR	Storage Temperature Range	-30 to +85			°C
Lead Solder Temperature(1/16 Inch Below Seating Plane)		260°C for 3 sec.			

ELECTRICAL/OPTICAL CHARACTERISTICS AT TA=25°C

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Iv	Luminous Intensity Per Segment	IF=2mA	H	1092		μcd
			S	1530		μcd
			K	1092		μcd
λp	Peak Emission Wavelength	IF=20mA	H	660		nm
			S	660		nm
			K	648		nm
λd	Domiant Emission Wavelength	IF=20mA	H	643		nm
			S	640		nm
			K	635		nm
Δλ	Spectral Line Half-Width	IF=20mA		20		nm
V F	Forward Voltage Per Segment	IF=2mA		1.65		V
IR	Reverse Current Per Segment	VR=5V		10		μA
Iv-m	Luminous Intensity Matching Rate	IF=20mA		1.5:1		

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TYPICAL ELECTRICAL/OPTICAL CHARACTERISTIC CURVES

Remark:

Dice code	①H	②S	③K
Lighting color	Hi-Red	Super-Red	Hi-Orange

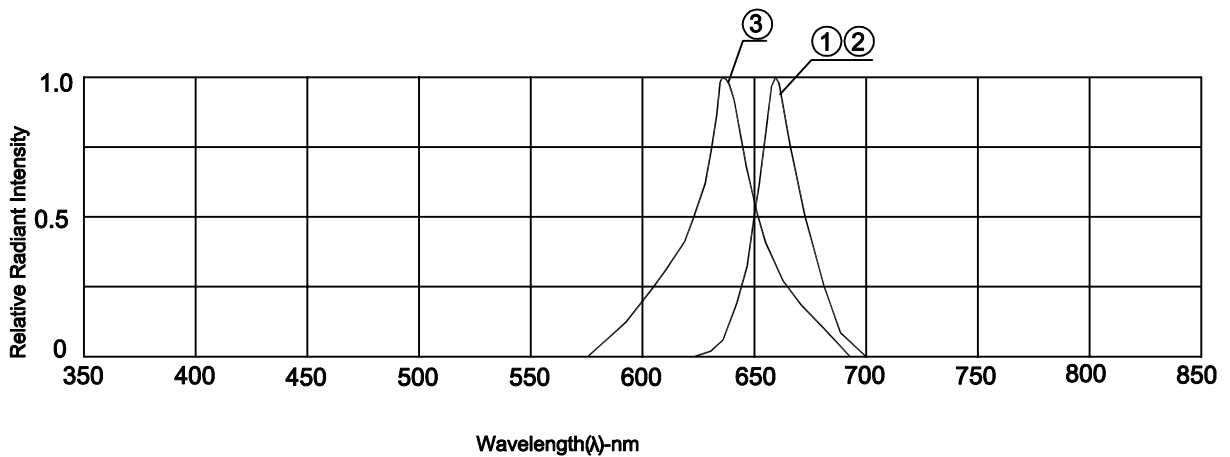


Fig1.RELATIVE INTENSITY VS. WAVELENGTH



TYPICAL ELECTRICAL/OPTICAL CHARACTERISTIC CURVES

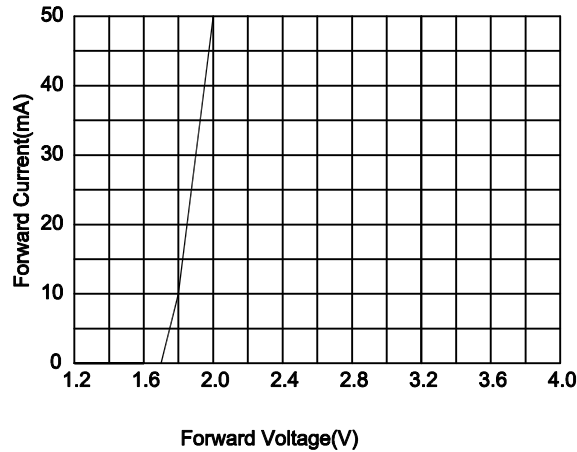


Fig2. FORWARD CURRENT VS. FORWARD VOLTAGE

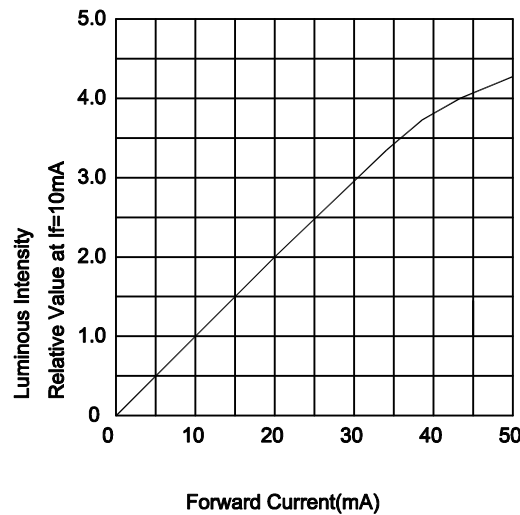


Fig3. RELATIVE LUMINOUS INTENSITY VS. FORWARD CURRENT



TYPICAL ELECTRICAL/OPTICAL CHARACTERISTIC CURVES

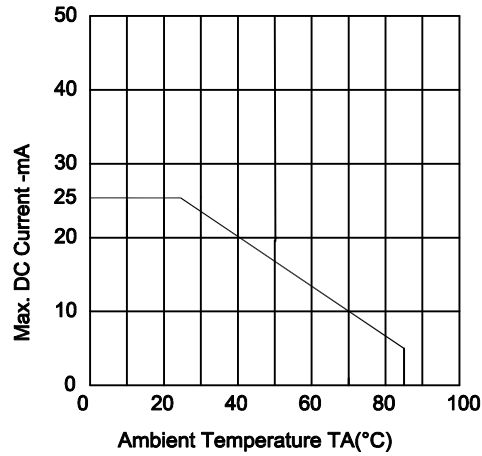


Fig4 MAX. ALLOWABLE DC CURRENT VS.AMBIENT TEMPERATURE.

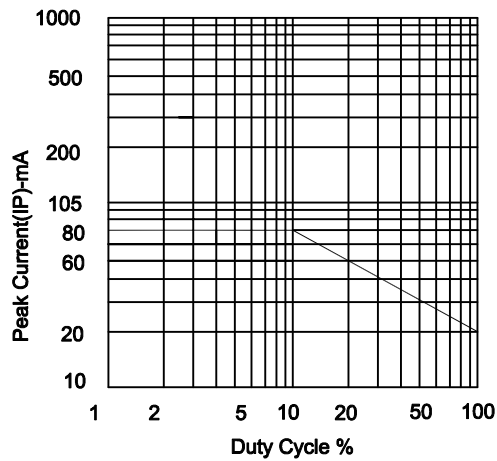


Fig5. MAX. PEAK CURRENT VS. DUTY CYCLE % (REFRESH RATE 1KHz)